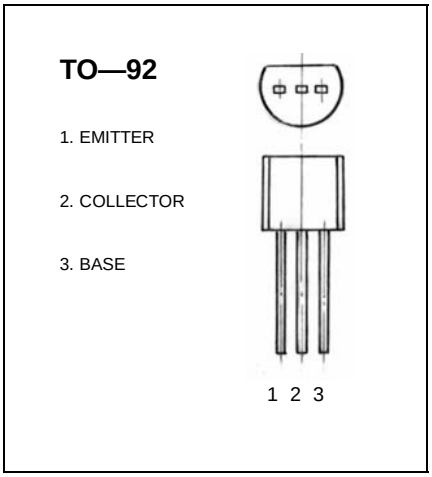
Transys Electronics LIMITED

TO-92 Plastic-Encapsulated Transistors

2N5172 TRANSISTOR (NPN)



FEATURES

Power dissipation

P_{CM} : 0.625 W (Tamb=25℃)

Collector current

I_{CM} : 0.5 A

Collector-base voltage

$V_{(BR)CBO}$: 25 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	Ic= 10μA, I_E=0	25			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	Ic= 10 mA, I_B=0	25			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E= 10μA, I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}= 25V, I_E=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= 5 V, I_C=0			0.1	μA
DC current gain	h_{FE}	V_{CE}= 10V, I_C= 10mA	100		500	
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=10mA, I_B=1mA			0.25	V
Base-emitter saturation voltage	V_{BE}(sat)	I_C=10mA, I_B=1mA			1.2	V